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SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

LV8011V — Bi-CMOS IC Forward/Reverse Motor Driver

Overview

LV8011V is a 1ch forward/reverse motor driver IC using D-MOS FET for output stage. As MOS circuit is used, it supports the PWM input. Its features are that the on resistance $(0.37\Omega \text{ typ})$ and current dissipation are low. It also provides protection functions such as heat protection circuit and reduced voltage detection and is optimal for the motors that need high-current (maximum peak current : 5A).

Absolute Maximum Ratings at Ta = 25°C, SGND = PGND = 0V

Parameter	Symbol	Conditions	Ratings	Unit
Maximum Power Source Voltage	VM max		-0.5 to 7.5	٧
(For load) Maximum Power Source Voltage	V _{CC} max			
(For control)	- CC		-0.5 to 6.0	V
Maximum Output Current	I _O max	DC	1.0	Α
	I _O peak1	t≤100ms, f = 2Hz	3.0	Α
	I _O peak2	t≤10ms, f = 2Hz	5.0	Α
Input Voltage	V _{IN} max		-0.5 to V _{CC} +0.5	V
Operating Temperature	Topr		-20 to +75	°C
Storage Temperature	Tstg		-55 to 150	°C
Allowable Power Dissipation	Pd	*Specified substrate	800	mW

^{*} When mounting the glass epoxy substrate 30mm×50mm×1.6mm.

Allowable Operating Range at SGND = PGND = 0V

Parameter	Symbol	Conditions	Ratings	Unit
Power Source Voltage (For load)	VM		2.0 to 6.5	V
Power Source Voltage (For control)	V _{CC}		4.5 to 5.5	V
Input Signal Voltage	V _{IN}		0 to V _{CC}	V
Input Signal Frequency	f max	duty = 50%	100	kHz
Charge-Pump Capacitor	C1, C2, C3		0.001 to 0.1	μF

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SANYO Semiconductor Co., Ltd.

LV8011V

Electric Characteristics at $Ta = 25^{\circ}C$, $V_{CC} = VM = 5.0V$, SGND = PGND = 0V

Parameter	Symbol	Conditions		Ratings			Damada
Farameter		Conditions	min	typ	max	Unit	Remarks
Standby Power Source Current for Load	IMO	EN = 0V			1.0	μΑ	1
Standby Power Source Current for Control	ICO	EN = 0V, IN1 = IN2 = TIN = 5V		50	100	μΑ	2
Operating Current Consumption	IC1	EN = 5V, VG when non-load.		0.7	1.2	mA	3
High Level Input Voltage	v_{IH}		2.5		VCC	V	
Low Level Input Voltage	V _{IL}		0		0.8	V	
High Level Input Current (IN1, IN2)	lін				1.0	μΑ	4
Low Level Input Current (IN1, IN2)	IIL		-1.0			μΑ	
Pull-up Resistance Value (EN, TIN)	RUP		50	100	200	kΩ	
Output ON Resistance	RON	Sum of top and bottom of ON resistance value.		0.37	0.60	Ω	5
Charge-Pump Voltage	VG		9.5	10.4	11	V	6
Low Voltage Detection Operating Voltage	VCS	V _{CC} Voltage	2.3	2.5	2.7	٧	7
Thermal Shutdown Operating Temperature	TTSD	*Design Target	150	180	210	°C	8
Charge-Pump Capacity (IG = 500μA)	VGLOAD		9.0	9.9		٧	9
IG Current Dissipation (Fin = 20kHz)	IG				350	μΑ	10
Charge Pump Start-up Time	TVG	$C1 = C2 = 0.01 \mu F$, $CVG = 0.1 \mu F$		0.5	1.0	ms	11
[Output Part]							
Turn-ON Time	TPLH			0.9	2.0	μs	12
Turn-OFF Time	TPHL			0.3	2.0	μs	12
[TOUT]	•	•	•		<u> </u>		•
Turn-ON Time	TOUT	C = 500pF		5.0	20	μs	12
Turn-OFF Time	TOFF	C = 500pF		5.0	20	μs	12

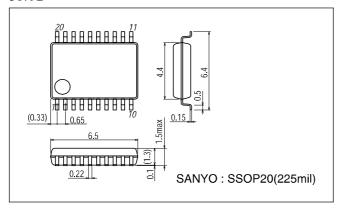
^{*} It is a design target value and measurement is not carried out.

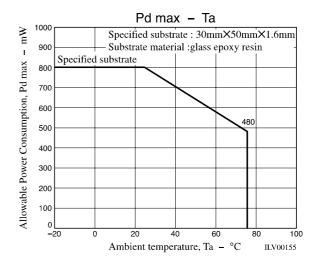
Remarks

- 1. It shows current dissipation of VM pin in output OFF state.
- 2. It shows current dissipation of $V_{\hbox{CC}}$ pin in stand-by state. (The standard current depends on EN pin pull-down resistance.)
- 3. It shows current dissipation of V_{CC} pin in state of EN = 5V (stand-by), including current dissipation of VG pin.
- 4. For IN1 and IN2 pins, no pull-down and pull-up resistance is needed. (High impedance pin)
- 5. It shows sum of upper and lower saturation voltages of OUT pin.
- 6. It controls charge-pump oscillation and makes specified voltage.
- 7. When low voltage is detected, the lower output is turned OFF.
- 8. When thermal protection circuit is activated, the lower output is turned OFF. When the heat temperature is fallen, it is turned ON again.
- 9. IG (VG pin load current) = 500μ F
- 10. It shows VG pin current dissipation in state of PWM input for IN pin.
- 11. It specifies start-up time from 10% to 90% when VG is in non-load state (when setting the capacitor between VG and GND to $0.1\mu F$ and V_{CC} is 5V).
- 12. It specifies 10% to 90% for start-up and 90% to 10% for shut-down.

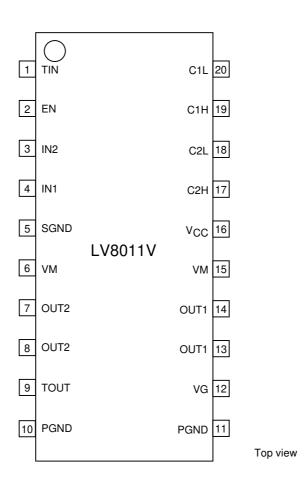
Package Dimensions

unit : mm 3179B

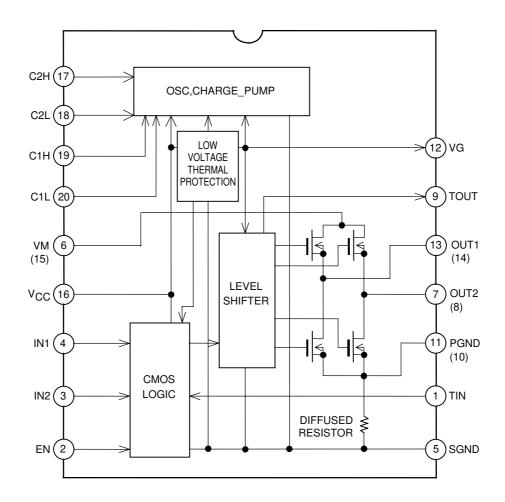




Pin Assignment



Block Diagram



True Value Table

Z: High-Impedance -: Don't care

EN	IN1	IN2	TIN	OUT1	OUT2	TOUT	Mode
Н	Н	Н	-	L	L	-	Brake
Н	Н	L	-	Н	L	-	Forward evolution
Н	L	Н	-	L	Н	-	Reverse rotation
Н	L	L	-	Z	Z	-	Stand by
L	-	-	-	L	L	L	Stdby
Н	-	-	Н	-	-	L	TR-OFF
Н	-	-	L	-	-	Н	TR-ON

^{*} For reduced voltage and thermal protection, the lower output is turned OFF and the motor drive stops.

LV8011V

Pin Description

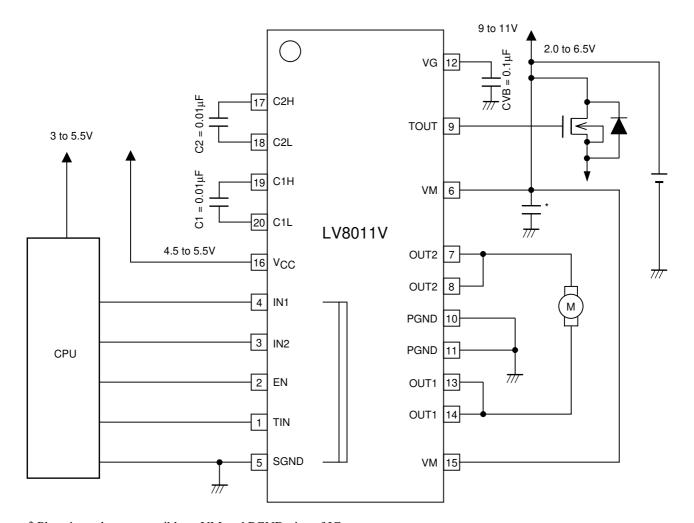
1	Cription		T
Pin no.	Pin name	Equivalent Circuit	Pin Explanation
20 18	C1L C2L	v _{cc}	Step-up Capacitor Connection Pin
		(20) (18)	
19 17	C1H C2H	C1H (19) C2H (17)	Step-up Capacitor Connection Pin
3	IN1 IN2	4 - W - W - W - W - W - W - W - W - W -	Driver Output Switch
2 1	EN TIN	2 - W - G G G G G G G G G G G G G G G G G	Logic Enable Pin TOUT Output Control Pin (Built-in Pull-up Resistance)
13 14	OUT1	VM	Driver Output Pin (Both 2 pins are Connected.)
		 	, , , , , , , , , , , , , , , , , , , ,
7 8	OUT2		

Continued on next page.

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Pin no.	Pin name	Equivalent Circuit	Pin Explanation
9	TOUT	9 VG	Step-up Voltage Output Pin
6	VM		Driver Power Source
15			(Both 2 pins are Connected.)
16	V _{CC}		Logic Power Source
12	VG	C2H 17 WW 12 WH 17 O	Driving Circuit Unit Power Source for Driver
5	SGND		Logic GND
10	PGND		Driver GND
11			(Both 2 pins are Connected.)

Application Circuit Diagram



^{*} Place it as close as possible to VM and PGND pins of IC.

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